

L Number	Hits	Search Text	DB	Time stamp
-	0	("nmos near capacitor").PN.	USPAT; US-PGPUB	2003/04/20 15:39
-	157	nmos near capacitor	USPAT; US-PGPUB	2003/04/20 16:27
-	2568	\$1mos near capacitor	USPAT; US-PGPUB	2003/04/20 16:28
-	52	(\$1mos near capacitor) and (low\$1pass near filter)	USPAT; US-PGPUB	2003/04/20 16:42
-	426	257/288.ccls.	USPAT; US-PGPUB	2003/04/20 17:13
-	516	257/368.ccls. not 257/288.ccls.	USPAT; US-PGPUB	2003/04/20 17:37
-	799	257/532.ccls. not (257/368.ccls. 257/288.ccls.)	USPAT; US-PGPUB	2003/04/20 18:07
-	82	(257/532.ccls. 257/595.ccls. 257/601.ccls.) and (\$1mos near capacitor\$1)	USPAT; US-PGPUB	2003/04/20 18:32
-	80	438/379.ccls.	USPAT; US-PGPUB	2003/04/20 18:15
-	77	438/394.ccls.	USPAT; US-PGPUB	2003/04/20 18:15
-	22	(438/197.ccls. 438/381.ccls.) and (\$1mos near capacitor\$1)	USPAT; US-PGPUB	2003/04/20 18:35
-	356	438/307.ccls.	USPAT; US-PGPUB	2003/04/20 18:46
-	248	327/558.ccls.	USPAT; US-PGPUB	2003/04/20 18:52
-	368	327/157.ccls. not 327/558.ccls.	USPAT; US-PGPUB	2003/04/20 18:52
-	10151	(gate with (p\$1type boron)) and ((source drain) with (p\$1type boron))	USPAT; US-PGPUB	2003/04/20 19:21
-	8023	((gate with (p\$1type boron)) and ((source drain) with (p\$1type boron))) and ((gate with (p\$1type boron)) same ((source drain) with (p\$1type boron)))	USPAT; US-PGPUB	2003/04/20 19:21
-	1273	((gate with (p\$1type boron)) and ((source drain) with (p\$1type boron))) and ((gate with (p\$1type boron)) same ((source drain) with (p\$1type boron))) and p\$1well	USPAT; US-PGPUB	2003/04/20 19:22
-	54	((((gate with (p\$1type boron)) and ((source drain) with (p\$1type boron))) and ((gate with (p\$1type boron)) same ((source drain) with (p\$1type boron)))) and p\$1well) and (\$1mos near capacitor)	USPAT; US-PGPUB	2003/04/20 19:36
-	3	(polysilicon near capacitor) same (electrode\$1 with (p\$type boron))	USPAT	2003/04/20 19:38
-	6	(polysilicon near capacitor) same (electrode\$1 with (p\$1type boron))	USPAT	2003/04/20 19:39
-	1146	capacitor near \$1mos	EPO; JPO; DERWENT; IBM_TDB	2003/04/20 19:40
-	29	(capacitor near \$1mos) and (gate with (p\$1type boron))	EPO; JPO; DERWENT; IBM_TDB	2003/04/20 19:50
-	555	(gate near p\$1type) and mos	USPAT	2003/04/20 19:51
-	323	((gate near p\$1type) and mos) and (gate near (n\$1type))	USPAT	2003/04/20 19:52
-	191	((gate near p\$1type) and mos) and (gate near (n\$1type)) and ((gate near n\$1type) with (gate near p\$1type))	USPAT	2003/04/20 20:11
-	223	capacitor with p\$1type with (diffusion implant\$7)	USPAT	2003/04/20 20:22
-	15	(capacitor with p\$1type with (diffusion implant\$7)) same (p\$1type with (upper top))	USPAT	2003/04/20 20:14
-	0	capacitor with (p\$1type near (upper adj electrode))	USPAT	2003/04/20 20:22

-	0	capacitor same (p\$1type near (upper adj electrode))	USPAT	2003/04/20 20:23
-	0	capacitor and (p\$1type near (upper adj electrode))	USPAT	2003/04/20 20:23
-	2	capacitor and (p\$1type near (top adj electrode))	USPAT	2003/04/20 20:23